

iscN-Channel MOSFET Transistor

TK8R2A06PL, ITK8R2A06PL

FEATURES

Low drain-source on-resistance:
R_{DS}(ON) = 8.2mΩ (V_{GS} = 10 V)

Enhancement mode:
Vth = 1.5 to 2.5V (VDS = 10 V, ID=0.3mA)

- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

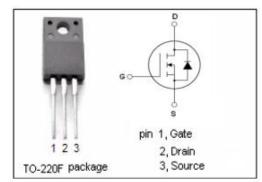


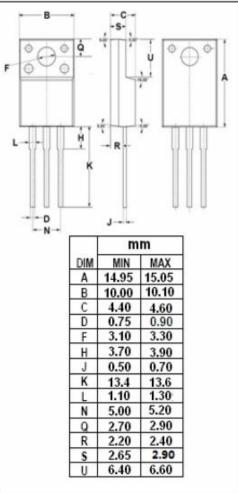
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

ABOOLOTE IMAXIMOM TXTITOO(Ta 20 0)						
SYMBOL	PARAMETER	VALUE	UNIT			
V _{DSS}	Drain-Source Voltage	60	V			
V _{GS}	Gate-Source Voltage	±20	V			
I _D	Drain Current-Continuous 50		А			
I _{DM}	Drain Current-Single Pulsed	260	А			
P _D	Total Dissipation @Tc=25°C	36	W			
Tj	Max. Operating Junction Temperature	175	$^{\circ}$ C			
T _{stg}	Storage Temperature	-55~175	$^{\circ}$			

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	4.16	°C/W
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C/W







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ELECTRICAL CHARACTERISTICS

isc website: www.iscsemi.cn

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 10mA	60			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = 10V; I _D =0.3mA	1.5		2.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =4.5V; I _D =8A			11.4	m Ω
		V _{GS} =10V; I _D =40A			8.2	
lgss	Gate-Source Leakage Current	V _{GS} = ±20V;V _{DS} = 0V			±0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 60V; V _{GS} = 0V			10	μА
V _{SDF}	Diode forward voltage	I _{DR} =50A, V _{GS} = 0 V			1.5	V

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